

RELIABILITY REPORT

FOR

MAX3225EUP+T

PLASTIC ENCAPSULATED DEVICES

May 14, 2012

# **MAXIM INTEGRATED PRODUCTS**

120 SAN GABRIEL DR. SUNNYVALE, CA 94086

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#### Conclusion

The MAX3225EUP+T successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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# I. Device Description

#### A. General

The MAX3224-MAX3227/MAX3244/MAX3245 are 3V-powered EIA/TIA-232 and V.28/V.24 communications interfaces with automatic shutdown/wakeup features and high data-rate capabilities. All devices achieve a 1µA supply current using Maxim's revolutionary AutoShutdown Plus(tm) feature. These devices automatically enter a low-power shutdown mode when the RS-232 cable is disconnected or the transmitters of the connected peripherals are inactive, and the UART driving the transmitter inputs is inactive for more than 30 seconds. They turn on again when they sense a valid transition at any transmitter or receiver input. AutoShutdown Plus saves power without changes to the existing BIOS or operating system. The MAX3225/MAX3227/MAX3245 also feature MegaBaud(tm) operation, guaranteeing 1Mbps for highspeed applications such as communicating with ISDN modems. The MAX3224/MAX3226/MAX3244 guarantee 250kbps operation. The transceivers have a proprietary low-dropout transmitter output stage enabling true RS-232 performance from a +3.0V to +5.5V supply with a dual charge pump. The charge pump requires only four small 0.1µF capacitors for operation from a 3.3V supply. The MAX3224-MAX3227 feature a logic-level output (READY) that asserts when the charge pump is regulating and the device is ready to begin transmitting. All devices are available in a space-saving TSSOP and SSOP packages.



## II. Manufacturing Information

A. Description/Function: 1µA Supply Current, 1Mbps, 3.0V to 5.5V, RS-232 Transceivers with

AutoShutdown Plus

B. Process: C3

C. Number of Device Transistors:

D. Fabrication Location: USA

E. Assembly Location: Malaysia, Philippines and Thailand

F. Date of Initial Production: April 17, 1998

# III. Packaging Information

A. Package Type: 20-pin TSSOP
B. Lead Frame: Copper

C. Lead Finish:

D. Die Attach:

Conductive

E. Bondwire:

Au (1 mil dia.)

F. Mold Material:

Epoxy with silica filler

G. Assembly Diagram:

#05-9000-4764

H. Flammability Rating:

Class UL94-V0

I. Classification of Moisture Sensitivity per

JEDEC standard J-STD-020-C

Level 1

J. Single Layer Theta Ja: 91°C/W
K. Single Layer Theta Jc: 20°C/W
L. Multi Layer Theta Ja: 73.8°C/W
M. Multi Layer Theta Jc: 20°C/W

# IV. Die Information

A. Dimensions: 91 X 159 mils

B. Passivation: Si<sub>3</sub>N<sub>4</sub>/SiO<sub>2</sub> (Silicon nitride/ Silicon dioxide)

C. Interconnect: Al/0.5%Cu with Ti/TiW Barrier

D. Backside Metallization: None

E. Minimum Metal Width: Metal1 = 0.8/Metal 2 = 1.2 microns (as drawn)

F. Minimum Metal Spacing: Metal1-2 = 1.2 microns (as drawn)

G. Bondpad Dimensions:

H. Isolation Dielectric: SiO<sub>2</sub>I. Die Separation Method: Wafer Saw



## V. Quality Assurance Information

A. Quality Assurance Contacts: Richard Aburano (Manager, Reliability Engineering)

Don Lipps (Manager, Reliability Engineering)

Bryan Preeshl (Vice President of QA)

B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.

0.1% For all Visual Defects.

C. Observed Outgoing Defect Rate: < 50 ppm</li>D. Sampling Plan: Mil-Std-105D

# VI. Reliability Evaluation

## A. Accelerated Life Test

The results of the 135C biased (static) life test are shown in Table 1. Using these results, the Failure Rate (  $\lambda$ ) is calculated as follows:

$$\frac{\lambda = \frac{1}{\text{MTTF}}}{\frac{1}{\text{MTTF}}} = \frac{1.83}{192 \times 4340 \times 398 \times 2} \text{ (Chi square value for MTTF upper limit)}$$

$$\frac{\lambda = \frac{1}{\text{MTTF}}}{\frac{1}{\text{MTTF}}} = \frac{1.83}{192 \times 4340 \times 398 \times 2} \text{ (where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)}$$

$$x = 2.8 \times 10^{-9}$$
  
 $x = 2.8 \text{ F.I.T. (60\% confidence level @ 25°C)}$ 

The following failure rate represents data collected from Maxim's reliability monitor program. Maxim performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at http://www.maxim-ic.com/qa/reliability/monitor. Cumulative monitor data for the C3 Process results in a FIT Rate of 0.78 @ 25C and 13.4 @ 55C (0.8 eV, 60% UCL)

## B. E.S.D. and Latch-Up Testing (lot J2DVBQ001A, D/C 1140)

The RU60-4 die type has been found to have all pins able to withstand a transient pulse of:

ESD-HBM: +/- 2500V per JEDEC JESD22-A114
ESD-CDM: +/- 750V per JEDEC JESD22-C101

Latch-Up testing has shown that this device withstands a current of +/- 250mA and overvoltage per JEDEC JESD78.



**Table 1**Reliability Evaluation Test Results

# MAX3225EUP+T

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES	COMMENTS
Static Life Test	(Note 1)				
	Ta = 135C	DC Parameters	80	0	J2DVBQ001A, D/C 1140
	Biased	& functionality	80	0	J2DZAQ001Y, D/C 1112
	Time = $192 \text{ hrs.}$		80	0	J2DZAQ002A, D/C 1115
			80	0	J2DZAQ003B, D/C 1117
			78	0	JABA2Q001A, D/C 1140

Note 1: Life Test Data may represent plastic DIP qualification lots.